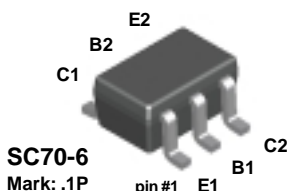
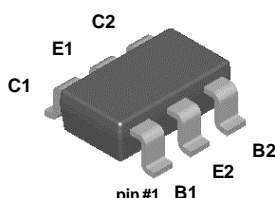


## FFB2222A



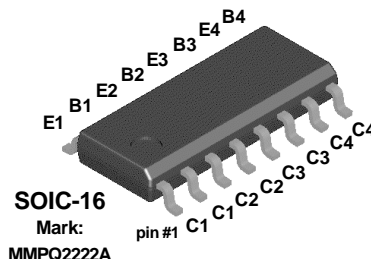
**SC70-6**  
Mark: .1P

## FMB2222A



**SuperSOT™-6**  
Mark: .1P  
Dot denotes pin #1

## MMPQ2222A



**SOIC-16**  
Mark: MMPQ2222A

NOTE: The pinouts are symmetrical; pin 1 and pin 4 are interchangeable. Units inside the carrier can be of either orientation and will not affect the functionality of the device.

## NPN Multi-Chip General Purpose Amplifier

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19.

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{CBO}$	Collector-Base Voltage	75	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current - Continuous	500	mA
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Characteristic	Max			Units
		FFB2222A	FMB2222A	MMPQ2222A	
$P_D$	Total Device Dissipation	300	700	1,000	mW
	Derate above $25^\circ\text{C}$	2.4	5.6	8.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180		$^\circ\text{C}/\text{W}$
	Effective 4 Die			125	$^\circ\text{C}/\text{W}$
	Each Die			240	$^\circ\text{C}/\text{W}$

## NPN Multi-Chip General Purpose Amplifier

(continued)

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	75			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\ \mu\text{A}, I_C = 0$	5.0			V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 60\text{ V}, I_E = 0$			10	nA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = 3.0\text{ V}, I_C = 0$			10	nA

### ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}^*$ $I_C = 150\text{ mA}, V_{CE} = 1.0\text{ V}^*$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}^*$	35 50 75 100 50 40		300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$			0.3 1.0	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$			1.2 2.0	V V

### SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 20\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$		300		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 100\text{ kHz}$		4.0		pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 100\text{ kHz}$		20		pF
NF	Noise Figure	$I_C = 100\ \mu\text{A}, V_{CE} = 10\text{ V},$ $R_S = 1.0\text{ k}\Omega, f = 1.0\text{ kHz}$		2.0		dB

### SWITCHING CHARACTERISTICS

$t_d$	Delay Time	$V_{CC} = 30\text{ V}, V_{BE(OFF)} = 0.5\text{ V},$		8		ns
$t_r$	Rise Time	$I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$		20		ns
$t_s$	Storage Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA},$		180		ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 15\text{ mA}$		40		ns

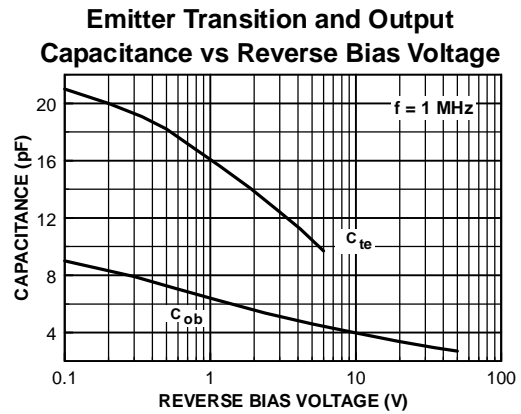
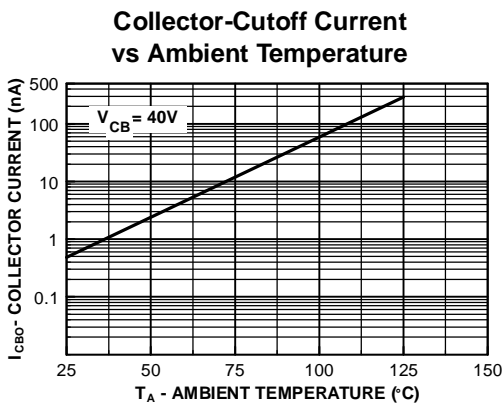
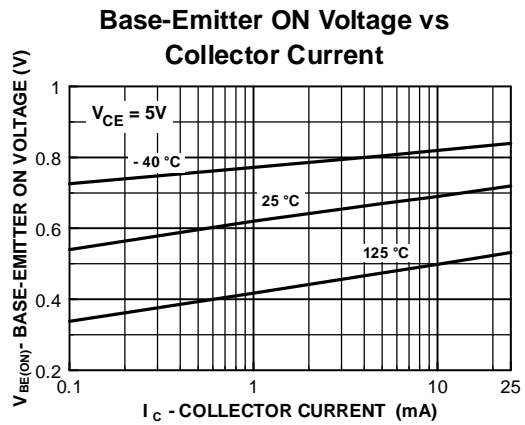
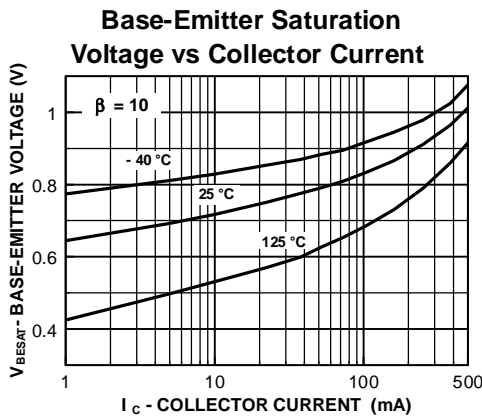
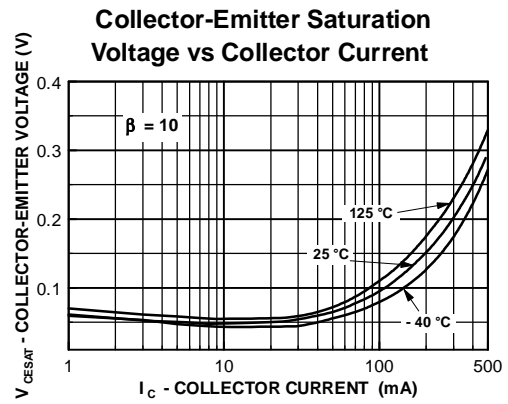
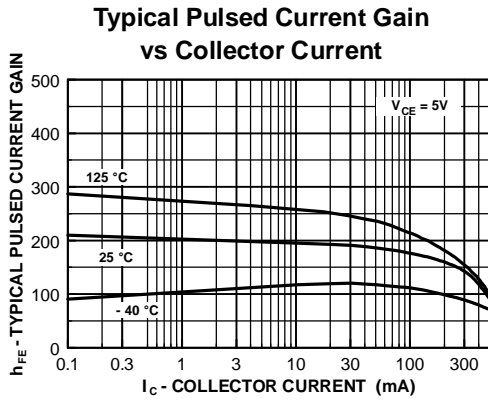
\*Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

### Spice Model

NPN (Is=14.34f Xti=3 Eg=1.11 Vaf=74.03 Bf=255.9 Ne=1.307 Ise=14.34f Ikf=.2847 Xtb=1.5 Br=6.092 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=7.306p Mjc=.3416 Vjc=.75 Fc=.5 Cje=22.01p Mje=.377 Vje=.75 Tr=46.91n Tf=411.1p Itf=.6 Vtf=1.7 Xtf=3 Rb=10)

FFB2222A / FMB2222A / MMPQ2222A

Typical Characteristics



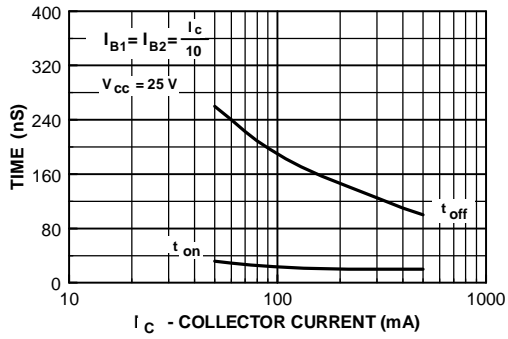
# NPN Multi-Chip General Purpose Amplifier

(continued)

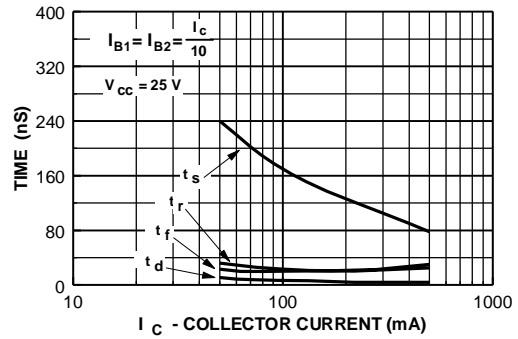
FFB2222A / FMB2222A / MMMPQ2222A

## Typical Characteristics (continued)

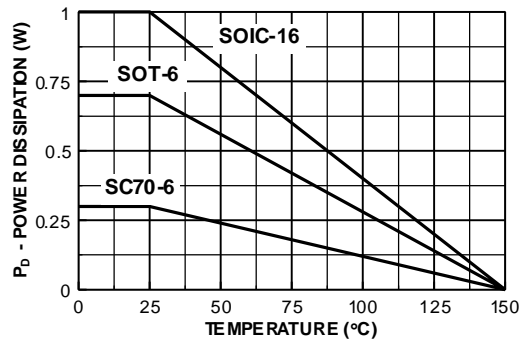
**Turn On and Turn Off Times vs Collector Current**



**Switching Times vs Collector Current**



**Power Dissipation vs Ambient Temperature**

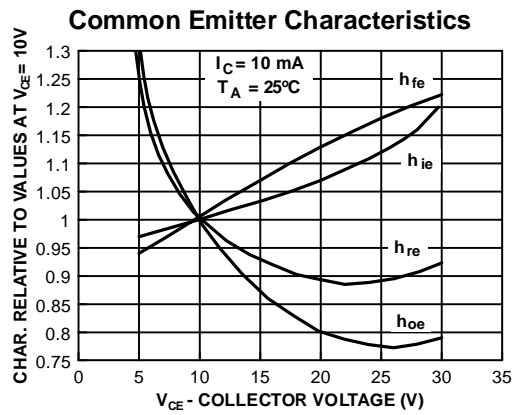
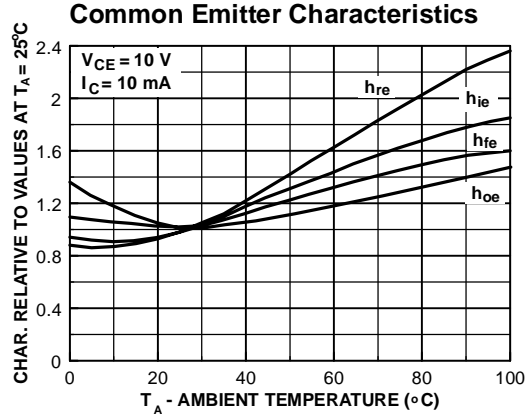
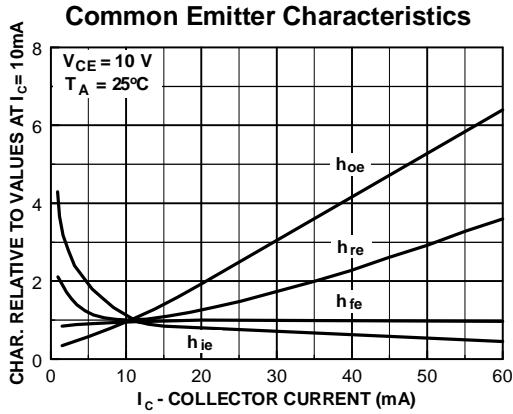


# NPN Multi-Chip General Purpose Amplifier

(continued)

FFB2222A / FMB2222A / MMPQ2222A

## Typical Common Emitter Characteristics (f = 1.0kHz)



Test Circuits

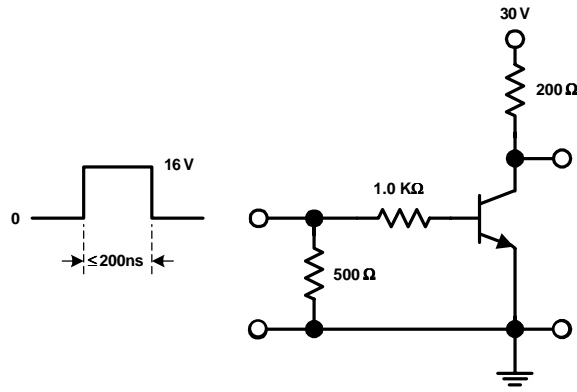


FIGURE 1: Saturated Turn-On Switching Time

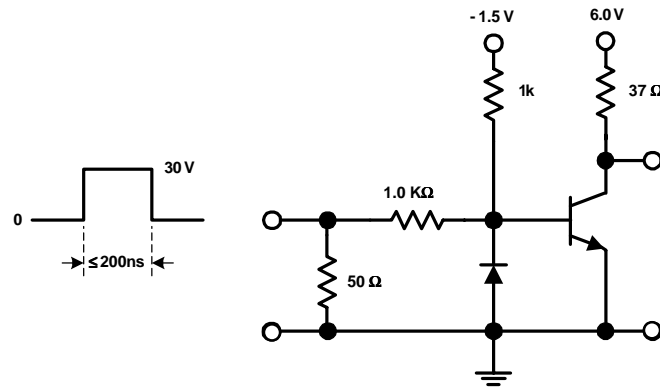


FIGURE 2: Saturated Turn-Off Switching Time

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